SPICE Device Model Si4401FDY



Vishay Siliconix

P-Channel 40 V (D-S) MOSFET

DESCRIPTION

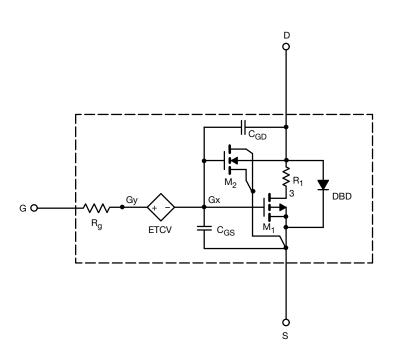
The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The sub-circuit model is extracted and optimized over the -55 °C to +125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- P-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- Apply for both linear and switching application
- Accurate over the -55 °C to +125 °C temperature range
- Model the gate charge

SUBCIRCUIT MODEL SCHEMATIC



Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits



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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$	1.7	-	V
Drain-source on-state resistance ^a	Р	$V_{GS} = -10 \text{ V}, I_D = -10 \text{ A}$	0.0118	0.0118	Ω
	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -10 \text{ A}$	0.0148	0.0150	
Forward transconductance ^a	g _{fs}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -10 \text{ A}$	41	45	S
Diode forward voltage	V _{SD}	I _F = -5 A	-0.77	-0.77	V
Dynamic ^b					
Input capacitance	C _{iss}	V_{DS} = -20 V, V_{GS} = 0 V, f = 1 MHz	4620	4000	pF
Output capacitance	Coss		284	280	
Reverse transfer capacitance	C _{rss}		269	270	
Total gate charge	0	$V_{DS} = -20 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -10 \text{ A}$	63	66	nC
	Qg	$V_{DS} = -20 \text{ V}, \text{ V}_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -10 \text{ A}$	31	31	
Gate-source charge	Q _{gs}		9.8	9.8	
Gate-drain charge	Q _{gd}		10	10	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing

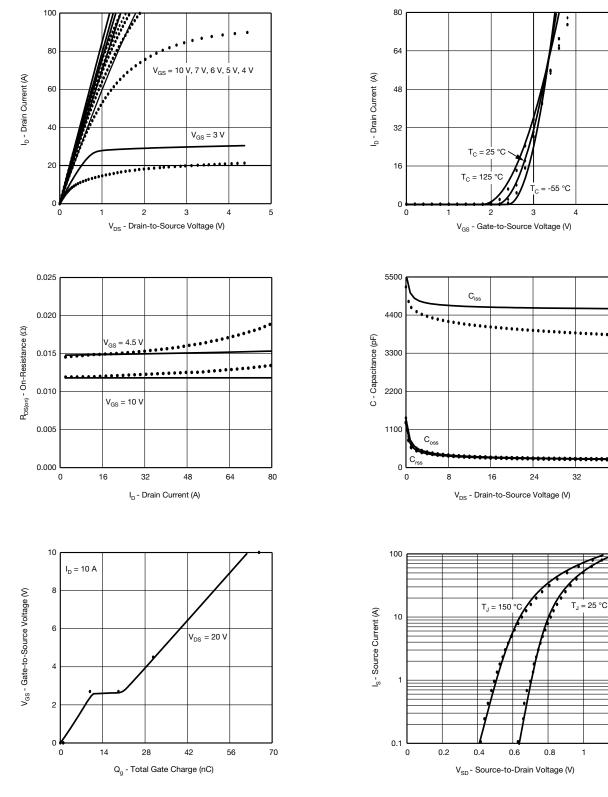


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COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C, unless otherwise noted)



Note

Dots and squares represent measured data
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